LDMOS 2-stage integrated Doherty MMIC Rev. 1 — 15 August 2019

Product profile 1.

1.1 General description

The BLM10D2327-40AB is a 2-stage fully integrated asymmetrical Doherty MMIC solution using Ampleon's state of the art GEN10 LDMOS technology. The carrier and peaking device, input splitter, output combiner and pre-match are integrated in a single package. This multiband device is perfectly suited as a final stage for small cells and massive MIMO applications in the frequency range from 2500 MHz to 2700 MHz. Available in PQFN outline.

Application performance Table 1.

Typical RF performance at T_{case} = 25 °C; I_{Dq} = 46 mA (carrier and peaking); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.4 V$. Test signal: 8-carrier LTE 20 MHz; PAR = 8.5 dB; measured in an Ampleon f = 2515 MHz to 2675 MHz integrated Doherty application circuit.

Test signal	f	V _{DS}	P _{L(AV)}	G _p	η D
	(MHz)	(V)	(W)	(dB)	(%)
8-carrier LTE 20 MHz (160 MHz) PAR = 8.5 dB	2595	28	5.75	28	44

1.2 Features and benefits

- Integrated input splitter
- Integrated output combiner
- **20** Ω output impedance thanks to integrated pre-match
- Very high efficiency thanks to asymmetry
- Designed for wideband operation (frequency 2500 MHz to 2700 MHz)
- Independent control of carrier and peaking bias
- Integrated ESD protection
- Source impedance 50 Ω ; high power gain
- For RoHS compliance see the product details on the Ampleon website

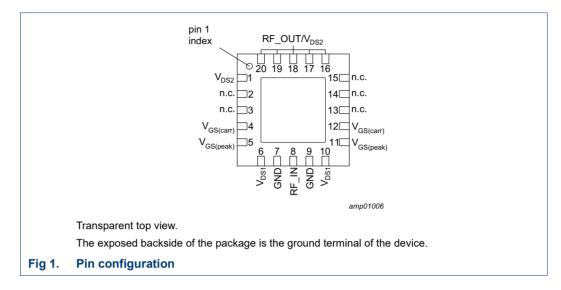
1.3 Applications

RF power MMIC for multi-carrier and multi-standard GSM, W-CDMA and LTE base stations in the 2500 MHz to 2700 MHz frequency range

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2. Pinning information

2.1 Pinning



2.2 Pin description

Table 2. Pin descr	iption	
Symbol	Pin	Description
V _{DS2}	1	drain-source voltage of final stages [1]
n.c.	2	not connected
n.c.	3	not connected
V _{GS(carr)}	4	gate-source voltage of carrier
V _{GS(peak)}	5	gate-source voltage of peaking
V _{DS1}	6	drain-source voltage of driver stages
GND	7	RF ground
RF_IN	8	RF input
GND	9	RF ground
V _{DS1}	10	drain-source voltage of driver stages
V _{GS(peak)}	11	gate-source voltage of peaking
V _{GS(carr)}	12	gate-source voltage of carrier
n.c.	13	not connected
n.c.	14	not connected
n.c.	15	not connected
RF_OUT/V _{DS2}	16	RF output / drain-source voltage of final stages
RF_OUT/V _{DS2}	17	RF output / drain-source voltage of final stages
RF_OUT/V _{DS2}	18	RF output / drain-source voltage of final stages
RF_OUT/V _{DS2}	19	RF output / drain-source voltage of final stages
RF_OUT/V _{DS2}	20	RF output / drain-source voltage of final stages

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BLM10D2327-40AB

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Table 2.	Pin descriptioncontinued					
Symbol		Pin	Description			
GND		flange	RF ground			

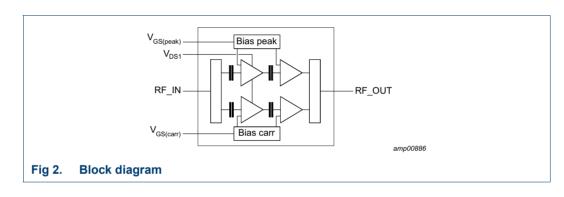
[1] $I_{max(DC)} \leq 500 \text{ mA}.$

3. Ordering information

Table 3. Ordering information

Type number	Package	Package						
	Name	Description	Version					
BLM10D2327-40AB	PQFN20	plastic thermal enhanced quad flat package; no leads; 20 terminals; body 8.0 x 8.0 x 2.1 mm	SOT1462-1					

4. Block diagram



5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage		-0.5	+65	V
V _{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	200	°C

[1] Continuous use at maximum temperature will affect the reliability. For details refer to the online MTF calculator.

6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Value	Unit
R _{th(j-c)}	thermal resistance from junction to case	T _{case} = 90 °C; P _L = 3.16 W	1 4.7	K/W
		T _{case} = 90 °C; P _L = 5.75 W	1 3.6	K/W

[1] When operated with a 1-carrier LTE with PAR = 7.6 dB.

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7. Characteristics

Table 6. DC characteristics

$T_{case} = 25 \mathrm{°C}.$								
Parameter	Conditions	Min	Тур	Max	Unit			
gate-source quiescent voltage	V _{DS} = 28 V; I _D = 45 mA	1.7	2.2	2.75	V			
gate leakage current	V _{GS} = 1 V; V _{DS} = 0 V	-	-	140	nA			
gate leakage current	V _{GS} = 1 V; V _{DS} = 0 V	-	-	140	nA			
ages								
drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	1.4	μA			
tages								
drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	1.4	μA			
	Parameter gate-source quiescent voltage gate leakage current gate leakage current ges drain leakage current tages	ParameterConditionsgate-source quiescent voltage $V_{DS} = 28 \text{ V}; I_D = 45 \text{ mA}$ gate leakage current $V_{GS} = 1 \text{ V}; V_{DS} = 0 \text{ V}$ gate leakage current $V_{GS} = 1 \text{ V}; V_{DS} = 0 \text{ V}$ gate leakage current $V_{GS} = 1 \text{ V}; V_{DS} = 0 \text{ V}$ agesdrain leakage currentVGS = 0 V; VDS = 28 Vtages	ParameterConditionsMingate-source quiescent voltage $V_{DS} = 28 \text{ V}; I_D = 45 \text{ mA}$ 1.7gate leakage current $V_{GS} = 1 \text{ V}; V_{DS} = 0 \text{ V}$ -gate leakage current $V_{GS} = 1 \text{ V}; V_{DS} = 0 \text{ V}$ -gate leakage current $V_{GS} = 1 \text{ V}; V_{DS} = 0 \text{ V}$ -agesdrain leakage current $V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$ -tages	ParameterConditionsMinTypgate-source quiescent voltage $V_{DS} = 28 \text{ V}; I_D = 45 \text{ mA}$ 1.72.2gate leakage current $V_{GS} = 1 \text{ V}; V_{DS} = 0 \text{ V}$ gate leakage current $V_{GS} = 1 \text{ V}; V_{DS} = 0 \text{ V}$ gate leakage current $V_{GS} = 1 \text{ V}; V_{DS} = 0 \text{ V}$ agestages	ParameterConditionsMinTypMaxgate-source quiescent voltage $V_{DS} = 28 \text{ V}$; $I_D = 45 \text{ mA}$ 1.72.22.75gate leakage current $V_{GS} = 1 \text{ V}$; $V_{DS} = 0 \text{ V}$ 140gate leakage current $V_{GS} = 1 \text{ V}$; $V_{DS} = 0 \text{ V}$ 140agesdrain leakage current $V_{GS} = 0 \text{ V}$; $V_{DS} = 28 \text{ V}$ 1.4tages			

Table 7.RF Characteristics

Typical RF performance at $T_{case} = 25 \ ^{\circ}C$; $V_{DS} = 28 \ V$; $I_{Dq} = 45 \ mA$ (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.4 \ V$; $P_{L(AV)} = 5.75 \ W$. $f = 2700 \ MHz$ measured in an Ampleon production circuit.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
G _p	power gain		27.5	29	31.1	dB
η _D	drain efficiency	P _L = 5.75 W (37.6 dBm)	38	43	-	%
		$P_L = P_{L(3dB)}$	46	50	-	%
RL _{in}	input return loss		-	-	-10	dB
P _{L(M)}	peak output power		44.7	45.7	-	dBm

8. Application information

Table 8.Typical performance

 $T_{case} = 25 \ ^{\circ}C$; $V_{DS} = 28 \ V$; $I_{Dq} = 46 \ mA$ (carrier and peaking); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.4 \ V$. Test signal: 1-carrier LTE 20 MHz; PAR = 7.6 dB; measured in an Ampleon f = 2515 MHz to 2675 MHz frequency band application circuit.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
P _{L(M)}	peak output power	f = 2595 MHz	[1]	-	46.3	-	dBm
$\phi_{s21}/\phi_{s21}(norm)$	normalized phase response	at 3 dB compression point; f = 2595 MHz	[2]	-	-28.5	-	0
η _D	drain efficiency	8.7 dB OBO (P _{L(AV)} = 37.6 dBm); f = 2595 MHz		-	44.5	-	%
		8.7 dB OBO (P _{L(AV)} = 37.6 dBm); f = 2595 MHz	[3]	-	44.1	-	%
G _p	power gain	P _{L(AV)} = 37.6 dBm; f = 2595 MHz		-	28.9	-	dB
B _{video}	video bandwidth	$P_{L(AV)}$ = 35 dBm set to obtain IMD3 = -25 dBc; f = 2595 MHz		-	371	-	MHz
G _{flat}	gain flatness	P _{L(AV)} = 37.6 dBm; f = 2515 MHz to 2675 MHz		-	0.5	-	dB

Table 8. Typical performance ...continued

 $T_{case} = 25 \ ^{\circ}C$; $V_{DS} = 28 \ V$; $I_{Dq} = 46 \ mA$ (carrier and peaking); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.4 \ V$. Test signal: 1-carrier LTE 20 MHz; PAR = 7.6 dB; measured in an Ampleon f = 2515 MHz to 2675 MHz frequency band application circuit.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ACPR _{20M}	adjacent channel power ratio (20M)	P _{L(AV)} = 37.6 dBm; f = 2595 MHz		-	-39.1	-	dBc
$\Delta G / \Delta T$	gain variation with temperature	f = 2595 MHz	[4]	-	-0.05	-	dB/°C
К	Rollett stability factor	T _{case} = -40 °C; f = 0.5 GHz to 85 GHz; VSWR at source > 20 : 1 at 2.6 GHz	<u>[4]</u>	-	>1	-	

[1] Test signal: 1-carrier W-CDMA; test model 1; 64 DPCH; PAR = 9.9 dB at 0.01 % probability CCDF.

[2] 25 ms CW power sweep measurement.

[3] Test signal: 8C LTE 20 MHz, PAR 8.5 dB at 0.01 % probability CCDF linearized.

[4] S-parameters measured with broadband demo board.

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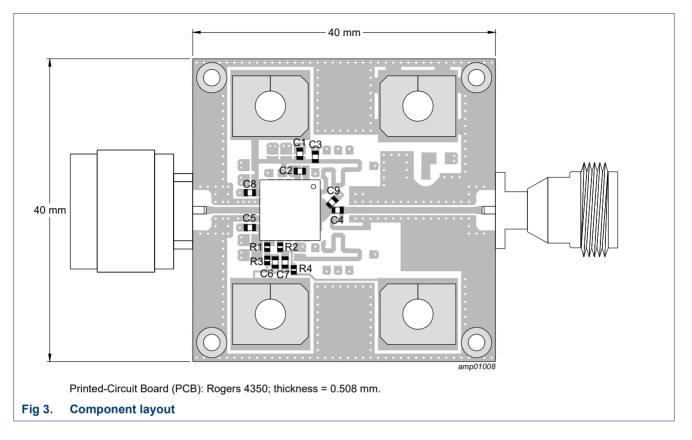
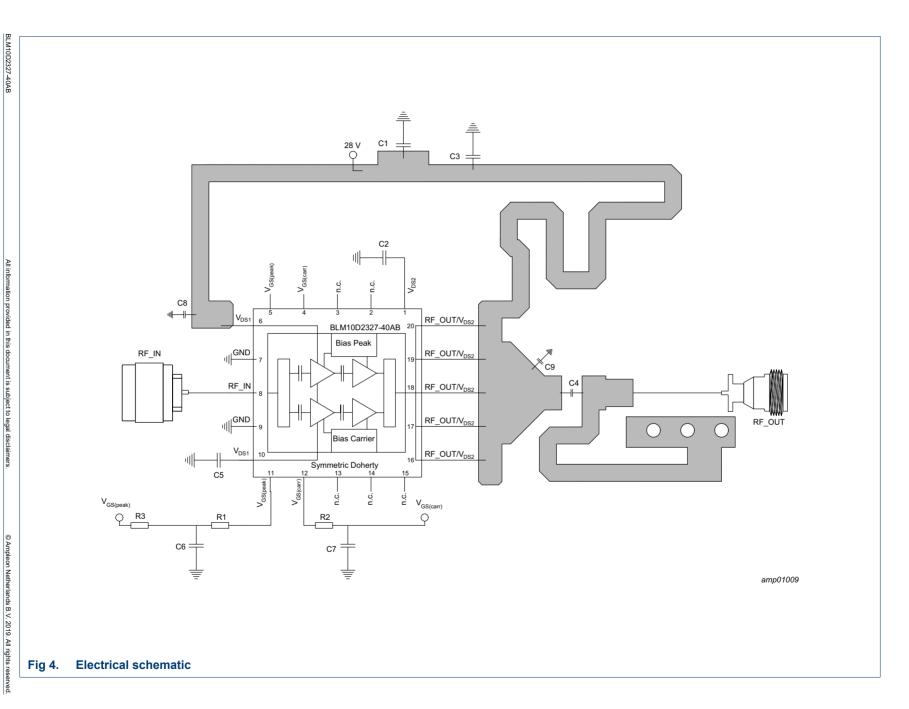


Table 9.Demo test circuit list of componentsSee Figure 3 for component layout.

Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	10 μF, 50 V	TDK: GC2012X5R1V106K; 805
C2	multilayer ceramic chip capacitor	100 nF	AVX: 06035D104KAT2A; 603
C3	multilayer ceramic chip capacitor	6.8 pF	Murata: GQM1885C2A6R8CB01; 603
C4	multilayer ceramic chip capacitor	1.5 pF	Murata: GQM1885C1A5R0CB01; 603
C6, C7	multilayer ceramic chip capacitor	10 μF, 6.3 V	AVX: 06036D106MAT2A; 603
C5, C8	multilayer ceramic chip capacitor	10 μF, 35 V	TDK: C2012X5R1V106K; 805
C9	multilayer ceramic chip capacitor	0.5 pF	Murata: GQM1885C2AR05CB01; 603
R1, R2, R3	resistor	0 Ω	Multicomp: 402
R4	resistor	2700 Ω	Multicomp: 402



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Product data sheet

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8.1 Ruggedness in a Doherty operation

The BLM10D2327-40AB is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 46 mA (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.42$ V; P_i corresponding to $P_{L(3dB)} - 5$ dB under $Z_S = 50 \Omega$ load; f = 2700 MHz (1-carrier W-CDMA); $T_{case} = 25$ °C.

8.2 Impedance information

Table 10. Typical impedance for optimum Doherty operation

Measured load-pull data; test signal: pulsed CW; $T_{case} = 25 \text{ °C}$; $V_{DS} = 28 \text{ V}$; $I_{Dq} = 45 \text{ mA}$ (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.4 \text{ V}$; $t_p = 100 \mu \text{s}$; $\delta = 10 \%$.

	tuned for optimun	tuned for optimum Doherty operation							
f	Z _L [1]	P _{L(3dB)}	G _{p(max)}	໗ _{add} [2]	໗ _{add} [3]				
(MHz)	(Ω)	(dBm)	(dB)	(%)	(%)				
2500	21.45 – j10.70	45.82	30.32	48.9	51.4				
2600	19.00 – j9.75	46.02	30.87	48.3	53.5				
2700	18.70 – j9.70	45.88	30.82	45.3	52.7				

[1] Reference package plane.

[2] At 37.6 dBm.

[3] At P_{L(3dB)}.

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9. Package outline

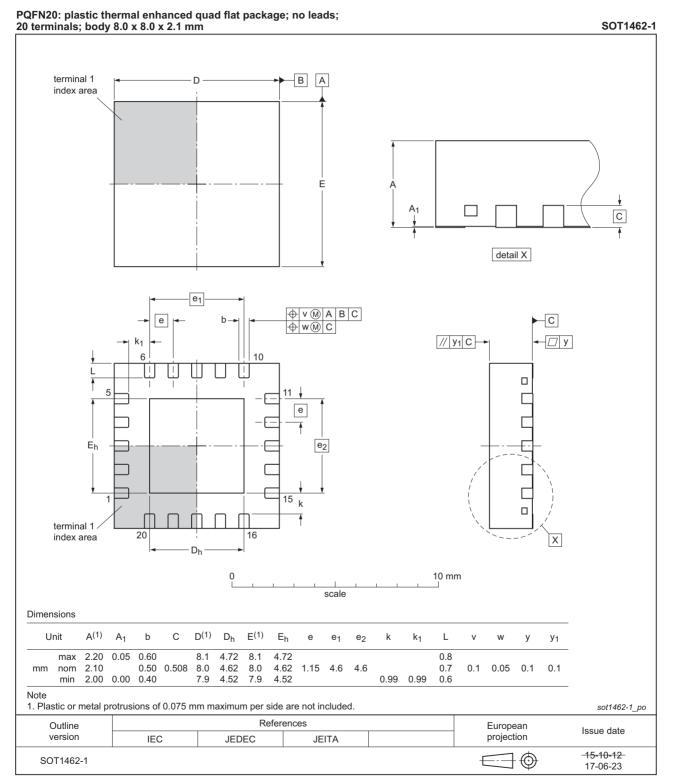


Fig 5. Package outline SOT1462-1 (PQFN20)

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10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 11.ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C3 [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	1C 🔼

[1] CDM classification C3 is granted to any part that passes after exposure to an ESD pulse of 1000 V.

[2] HBM classification 1C is granted to any part that passes after exposure to an ESD pulse of 1000 V.

11. Abbreviations

Table 12. Abbreviations				
Acronym	Description			
CW	Continuous Wave			
ESD	ElectroStatic Discharge			
GEN10	Tenth Generation			
GSM	Global System for Mobile Communications			
LDMOS	Laterally Diffused Metal Oxide Semiconductor			
LTE	Long Term Evolution			
MMIC	Monolithic Microwave Integrated Circuit			
MIMO	Multiple Input Multiple Output			
MTF	Median Time to Failure			
ОВО	Output Back Off			
PAR	Peak-to-Average Ratio			
RoHS	Restriction of Hazardous Substances			
VSWR	Voltage Standing Wave Ratio			
W-CDMA	Wideband Code Division Multiple Access			

12. Revision history

Table 13. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
BLM10D2327-40AB v.1	20190815	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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